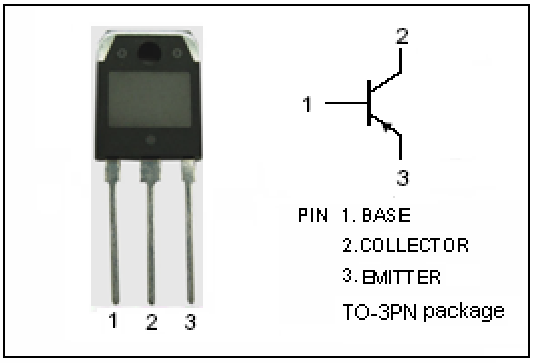
isc Silicon PNP Power Transistor 2SB775



DESCRIPTION

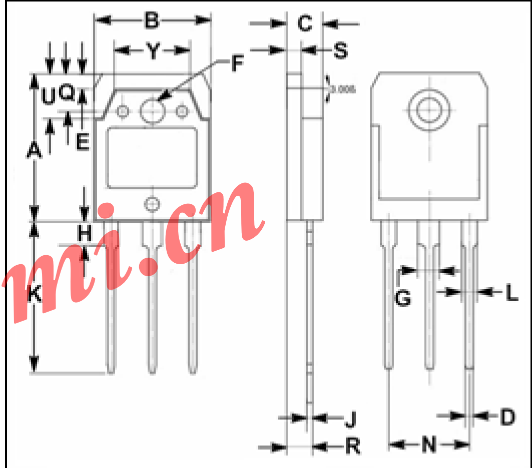
- Collector-Emitter Breakdown Voltage-
  : $V_{(BR)CEO}$= -85V(Min)
- Good Linearity of h_{FE}
- High Current Capability
- Wide Area of Safe Operation
- Complement to Type 2SD895

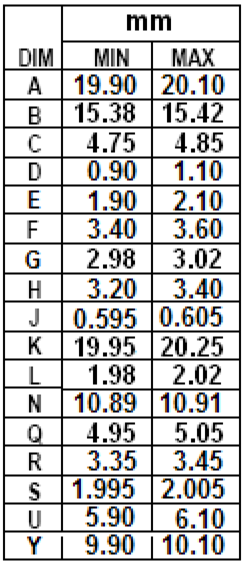
APPLICATIONS

- Designed for 35W audio frequency output applications.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-100	V
V_{CEO}	Collector-Emitter Voltage	-85	V
V_{EBO}	Emitter-Base Voltage	-6	V
I_C	Collector Current-Continuous	-6	A
I_{CP}	Collector Current-Pulse	-10	A
P_C	Collector Power Dissipation @ T_C=25℃	60	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-40~150	℃





	mm	
DIM	MIN	MAX
A	19.90	20.10
B	15.38	15.42
C	4.75	4.85
D	0.90	1.10
E	1.90	2.10
F	3.40	3.60
G	2.98	3.02
H	3.20	3.40
J	0.595	0.605
K	19.95	20.25
L	1.98	2.02
N	10.89	10.91
Q	4.95	5.05
R	3.35	3.45
S	1.995	2.005
U	5.90	6.10
Y	9.90	10.10

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= -50mA ; R_{BE}=∞	-85			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	I_C= -5mA; I_E= 0	-100			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I_E= -5mA; I_C= 0	-6			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= -4A; I_B= -0.4A			-2.0	V
$V_{BE(on)}$	Base -Emitter On Voltage	I_C= -1A; V_{CE}= -5V			-1.5	V
I_{CBO}	Collector Cutoff Current	V_{CB}= -40V; I_E=0			-100	μA
I_{EBO}	Emitter Cutoff Current	V_{EB}= -4V; I_C=0			-100	μA
h_{FE-1}	DC Current Gain	I_C= -1A; V_{CE}= -5V	60		200	
h_{FE-2}	DC Current Gain	I_C= -3A; V_{CE}= -5V	20			
C_{OB}	Output Capacitance	V_{CB}= -10V; f_{test}= 1.0MHz		160		pF
f_T	Current-Gain—Bandwidth Product	I_C=-1A; V_{CE}= -5V		18		MHz

Switching times

t_{on}	Turn-on Time	I_C= -1A ,R_L= 20Ω , I_{B1}= -I_{B2}= -0.1A,V_{CC}=-20V		0.12		μs
t_{stg}	Storage Time			1.29		μs
t_f	Fall Time			0.36		μs

◆ h_{FE-1} Classifications

D	E
60-120	100-200